Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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S-5731 Series

HIGH-WITHSTAND VOLTAGE HIGH-SPEED UNIPOLAR DETECTION TYPE HALL EFFECT SWITCH IC

www.sii-ic.com

Rev.1.1_00

This IC, developed by CMOS technology, is a unipolar detection type Hall effect switch IC with high-withstand voltage, high-speed detection and high-accuracy magnetic characteristics.
The output voltage changes when this IC detects the intensity level of magnetic flux density. Using this IC with a magnet makes it possible to detect the open / close and rotation status in various devices.
This IC includes an output current limit circuit.
High-density mounting is possible by using the small SOT-23-3 package.
Due to its high-accuracy magnetic characteristics, this IC can make operation's dispersion in the system combined with magnet smaller.

SII Semiconductor Corporation offers a "magnetic simulation service" that provides the ideal combination of magnets and our Hall effect ICs for customer systems. Our magnetic simulation service will reduce prototype production, development period and development costs. In addition, it will contribute to optimization of parts to realize high cost performance.
For more information regarding our magnetic simulation service, contact our sales office.

■ Features

- Pole detection*1: Detection of S pole, detection of N pole
- Output logic*1: Active "L", active "H"
- Output form*1: Nch open-drain output, Nch driver + built-in pull-up resistor
- Magnetic sensitivity*1: B_{OP} = 3.0 mT typ., B_{OP} = 6.0 mT typ.
- Chopping frequency: f_C = 250 kHz typ.
- Output delay time: t_D = 16.0 µs typ.
- Power supply voltage range: V_{DD} = 3.5 V to 26.0 V
- Built-in regulator
- Built-in output current limit circuit
- Operation temperature range: Ta = –40°C to +85°C
- Lead-free (Sn 100%), halogen-free

***1.** The option can be selected.

■ Applications

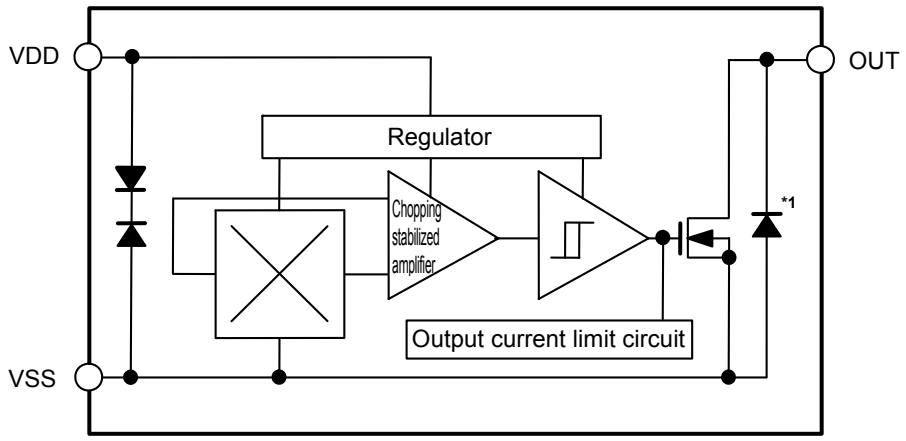
- Home appliance
- DC brushless motor
- Housing equipment
- Industrial equipment

■ Package

- SOT-23-3

■ Block Diagrams

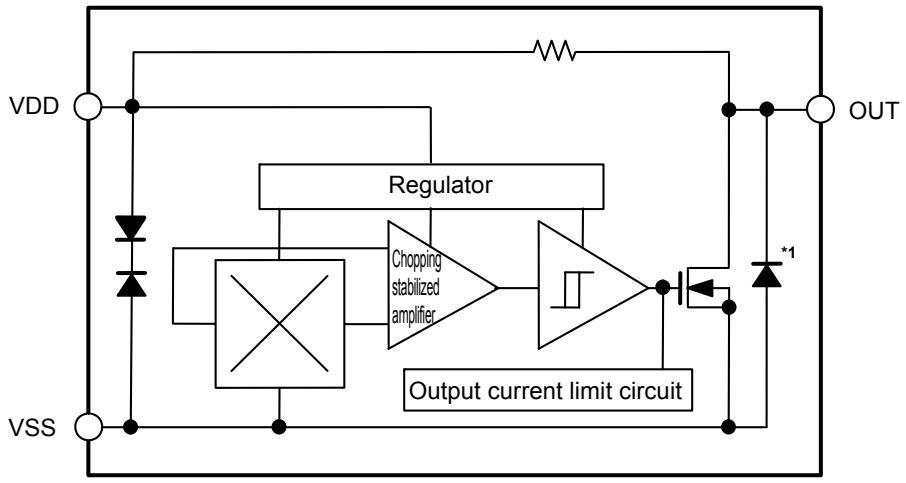
1. Nch open-drain output product



***1.** Parasitic diode

Figure 1

2. Nch driver + built-in pull-up resistor product

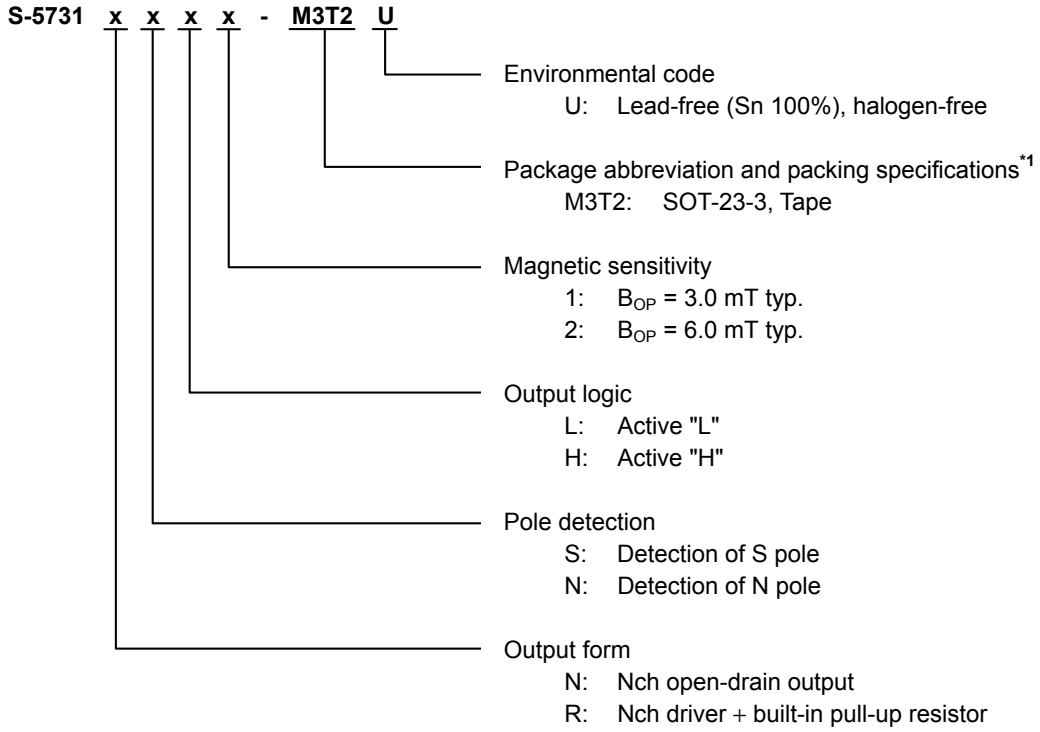


***1.** Parasitic diode

Figure 2

■ Product Name Structure

1. Product name



***1.** Refer to the tape drawing.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
SOT-23-3	MP003-C-P-SD	MP003-C-C-SD	MP003-Z-R-SD

3. Product name list

Table 2

Product Name	Output Form	Pole Detection	Output Logic	Magnetic Sensitivity (B_{OP})
S-5731NSL1-M3T2U	Nch open-drain output	S pole	Active "L"	3.0 mT typ.
S-5731NSL2-M3T2U	Nch open-drain output	S pole	Active "L"	6.0 mT typ.
S-5731NNL2-M3T2U	Nch open-drain output	N pole	Active "L"	6.0 mT typ.
S-5731RSL1-M3T2U	Nch driver + built-in pull-up resistor	S pole	Active "L"	3.0 mT typ.

Remark Please contact our sales office for products other than the above.

■ Pin Configuration

1. SOT-23-3

Top view

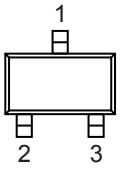


Figure 3

Table 3

Pin No.	Symbol	Description
1	VSS	GND pin
2	VDD	Power supply pin
3	OUT	Output pin

■ Absolute Maximum Ratings

Table 4

(Ta = +25°C unless otherwise specified)

Item		Symbol	Absolute Maximum Rating	Unit
Power supply voltage		V_{DD}	V_{SS} − 0.3 to V_{SS} + 28.0	V
Output current		I_{OUT}	20	mA
Output voltage	Nch open-drain output product	V_{OUT}	V_{SS} − 0.3 to V_{SS} + 28.0	V
	Nch driver + built-in pull-up resistor product		V_{SS} − 0.3 to V_{DD} + 0.3	V
Operation ambient temperature		T_{opr}	−40 to +85	°C
Storage temperature		T_{stg}	−40 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 5

Item	Symbol	Condition		Min.	Typ.	Max.	Unit
Junction-to-ambient thermal resistance*1	θ_{ja}	SOT-23-3	Board A	−	200	−	°C/W
			Board B	−	165	−	°C/W
			Board C	−	−	−	°C/W
			Board D	−	−	−	°C/W
			Board E	−	−	−	°C/W

***1.** Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ **Power Dissipation**" and "**Test Board**" for details.

■ Electrical Characteristics

Table 6

(Ta = +25°C, V_{DD} = 12.0 V, V_{SS} = 0 V unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Power supply voltage	V_{DD}	–	3.5	12.0	26.0	V	–
Current consumption	I_{DD}	Nch open-drain output product Average value	–	3.0	4.0	mA	1
		Nch driver + built-in pull-up resistor product Average value, V_{OUT} = "H"	–	3.0	4.0	mA	1
Output voltage	V_{OUT}	Nch open-drain output product Output transistor Nch, V_{OUT} = "L", I_{OUT} = 10 mA	–	–	0.4	V	2
		Nch driver + built-in pull-up resistor product Output transistor Nch, V_{OUT} = "L", I_{OUT} = 10 mA	–	–	0.5	V	2
Output drop voltage	V_D	Nch driver + built-in pull-up resistor product V_{OUT} = "H", $V_D = V_{DD} - V_{OUT}$	–	–	20	mV	2
Leakage current	I_{LEAK}	Nch open-drain output product Output transistor Nch, V_{OUT} = "H" = 26.0 V	–	–	10	μA	3
Output limit current	I_{OM}	V_{OUT} = 12.0 V	22	–	70	mA	3
Output delay time	t_D	–	–	16.0	–	μs	–
Chopping frequency	f_C	–	–	250	–	kHz	–
Start up time	t_{PON}	–	–	30	–	μs	4
Output rise time	t_R	Nch open-drain output product C = 20 pF, R = 820 Ω	–	–	2.0	μs	5
		Nch driver + built-in pull-up resistor product C = 20 pF	–	–	6.0	μs	5
Output fall time	t_F	C = 20 pF, R = 820 Ω	–	–	2.0	μs	5
Pull-up resistor	R_L	Nch driver + built-in pull-up resistor product	7	10	13	kΩ	–

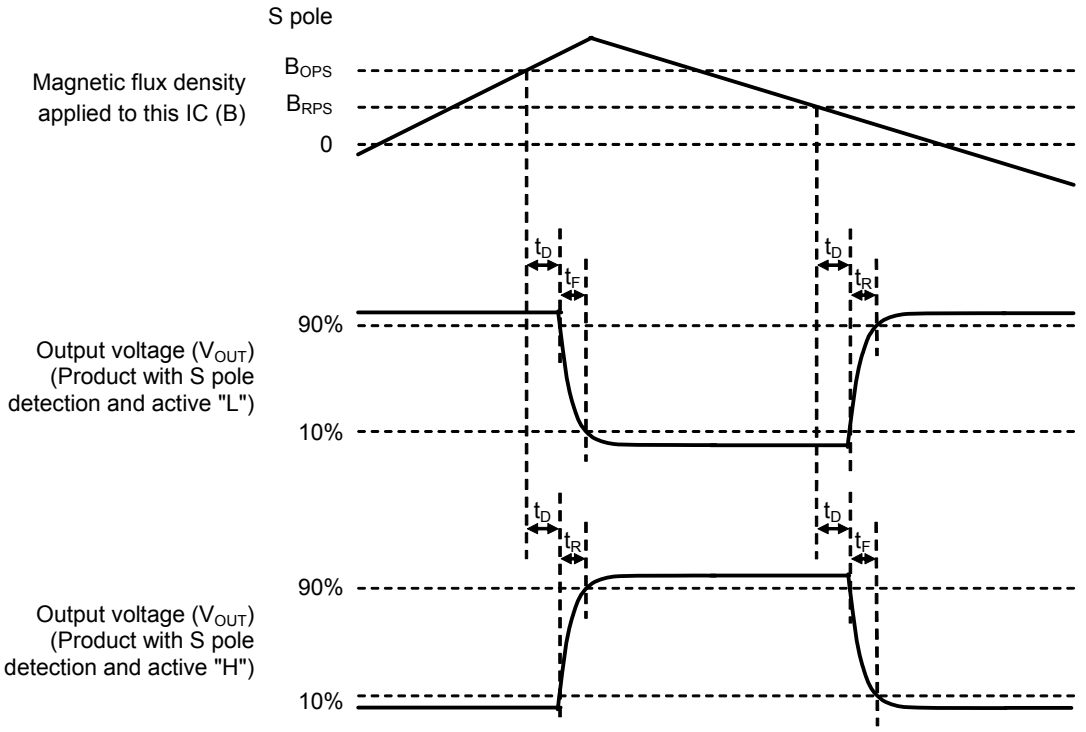


Figure 4 Operation Timing

■ Magnetic Characteristics

1. Product with S pole detection

1. 1 Product with B_{OP} = 3.0 mT typ.

Table 7

(Ta = +25°C, V_{DD} = 12.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Operation point*1	S pole	B_{OPS}	–	1.5	3.0	4.5	mT	4
Release point*2	S pole	B_{RPS}	–	1.0	2.0	3.3	mT	4
Hysteresis width*3	S pole	B_{HYSS}	$B_{HYSS} = B_{OPS} - B_{RPS}$	–	1.0	–	mT	4

1. 2 Product with B_{OP} = 6.0 mT typ.

Table 8

(Ta = +25°C, V_{DD} = 12.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Operation point*1	S pole	B_{OPS}	–	3.0	6.0	9.0	mT	4
Release point*2	S pole	B_{RPS}	–	2.5	4.5	7.5	mT	4
Hysteresis width*3	S pole	B_{HYSS}	$B_{HYSS} = B_{OPS} - B_{RPS}$	–	1.5	–	mT	4

2. Product with N pole detection

2. 1 Product with B_{OP} = 6.0 mT typ.

Table 9

(Ta = +25°C, V_{DD} = 12.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Operation point*1	N pole	B_{OPN}	–	–9.0	–6.0	–3.0	mT	4
Release point*2	N pole	B_{RPN}	–	–7.5	–4.5	–2.5	mT	4
Hysteresis width*3	N pole	B_{HYSN}	$B_{HYSN} = \lvert B_{OPN} - B_{RPN} \rvert$	–	1.5	–	mT	4

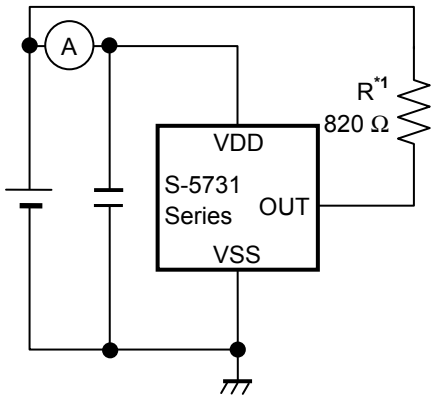
***1.** B_{OPN}, B_{OPS}: Operation points
B_{OPN} and B_{OPS} are the values of magnetic flux density when the output voltage (V_{OUT}) changes after the magnetic flux density applied to this IC by the magnet (N pole or S pole) is increased (by moving the magnet closer).
Even when the magnetic flux density exceeds B_{OPN} or B_{OPS}, V_{OUT} retains the status.

***2.** B_{RPN}, B_{RPS}: Release points
B_{RPN} and B_{RPS} are the values of magnetic flux density when the output voltage (V_{OUT}) changes after the magnetic flux density applied to this IC by the magnet (N pole or S pole) is decreased (the magnet is moved further away).
Even when the magnetic flux density falls below B_{RPN} or B_{RPS}, V_{OUT} retains the status.

***3.** B_{HYSN}, B_{HYSS}: Hysteresis widths
B_{HYSN} and B_{HYSS} are the difference between B_{OPN} and B_{RPN}, and B_{OPS} and B_{RPS}, respectively.

Remark The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

■ Test Circuits



***1.** Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

Figure 5 Test Circuit 1

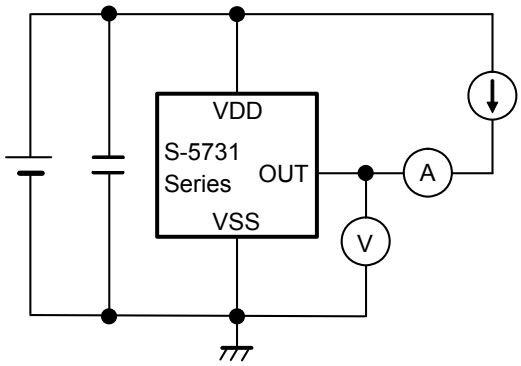


Figure 6 Test Circuit 2

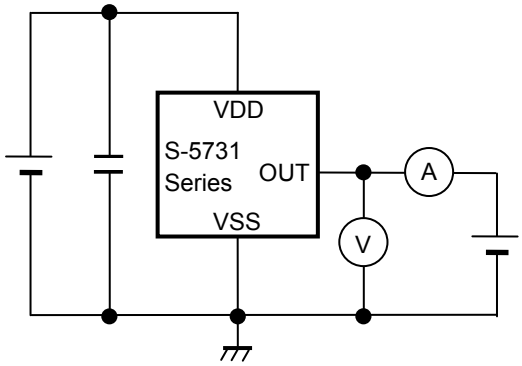
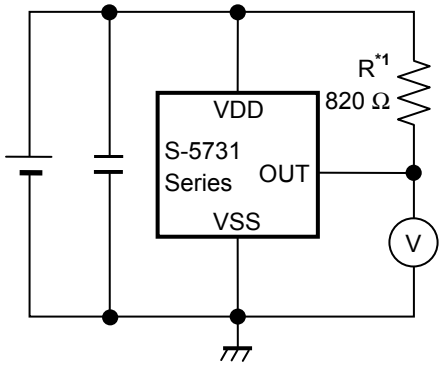
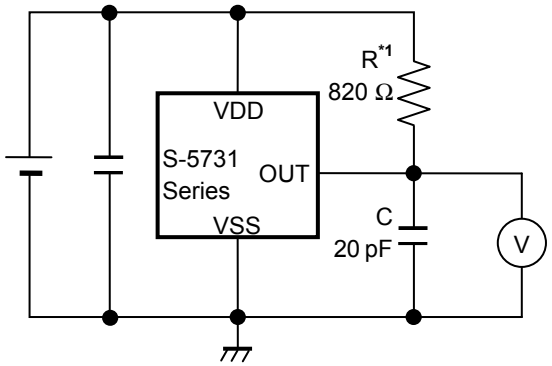


Figure 7 Test Circuit 3



***1.** Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

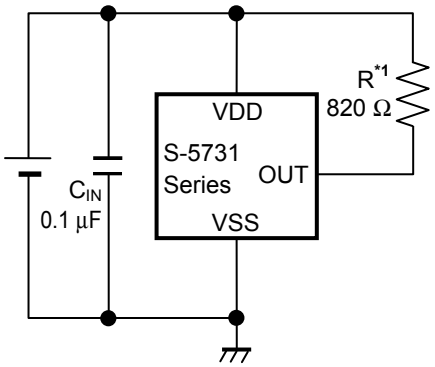
Figure 8 Test Circuit 4



***1.** Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

Figure 9 Test Circuit 5

■ Standard Circuit



***1.** Resistor (R) is unnecessary for Nch driver + built-in pull-up resistor product.

Figure 10

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

1. Direction of applied magnetic flux

This IC detects the magnetic flux density which is vertical to the marking surface.
Figure 11 shows the direction in which magnetic flux is being applied.

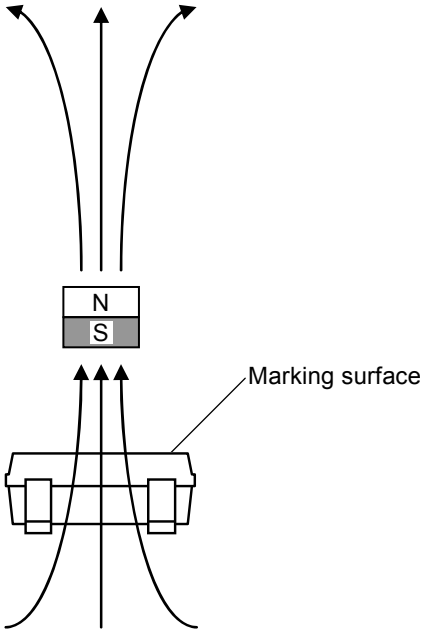


Figure 11

2. Position of Hall sensor

Figure 12 shows the position of Hall sensor.
The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.
The following also shows the distance (typ. value) between the marking surface and the chip surface of a package.

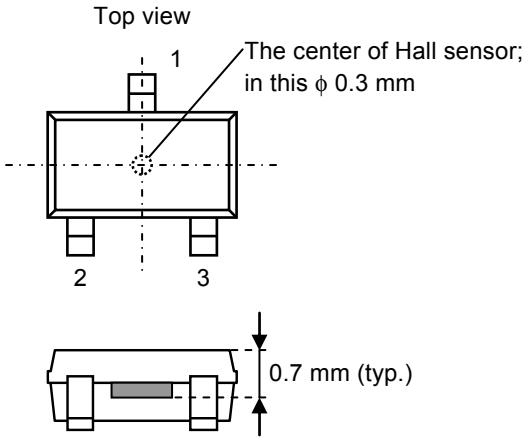


Figure 12

3. Basic operation

This IC changes the output voltage (V_{OUT}) according to the level of the magnetic flux density (N pole or S pole) applied by a magnet.
The following explains the operation when the output logic is active "L".

3. 1 Product with S pole detection

When the magnetic flux density of the S pole perpendicular to the marking surface exceeds the operation point (B_{OPS}) after the S pole of a magnet is moved closer to the marking surface of this IC, V_{OUT} changes from "H" to "L". When the S pole of a magnet is moved further away from the marking surface of this IC and the magnetic flux density is lower than the release point (B_{RPS}), V_{OUT} changes from "L" to "H".
Figure 13 shows the relationship between the magnetic flux density and V_{OUT}.

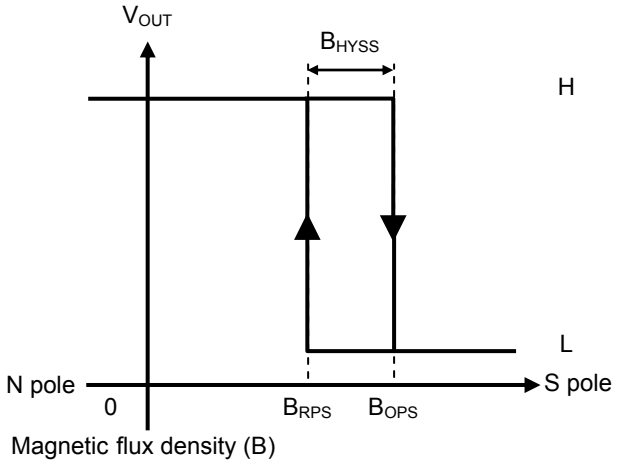


Figure 13

3. 2 Product with N pole detection

When the magnetic flux density of the N pole perpendicular to the marking surface exceeds the operation point (B_{OPN}) after the N pole of a magnet is moved closer to the marking surface of this IC, V_{OUT} changes from "H" to "L". When the N pole of a magnet is moved further away from the marking surface of this IC and the magnetic flux density of the N pole is lower than the release point (B_{RPN}), V_{OUT} changes from "L" to "H".
Figure 14 shows the relationship between the magnetic flux density and V_{OUT}.

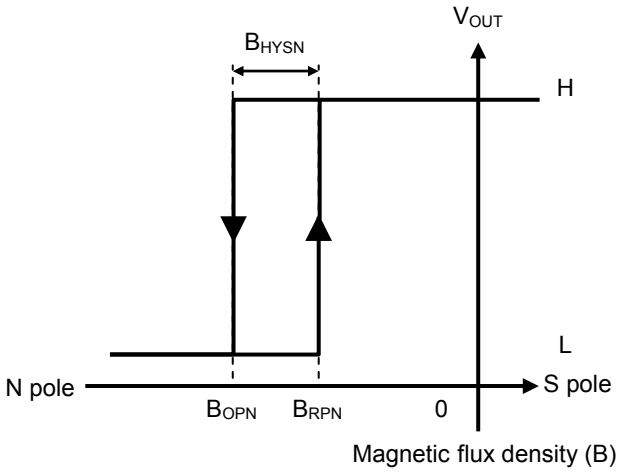


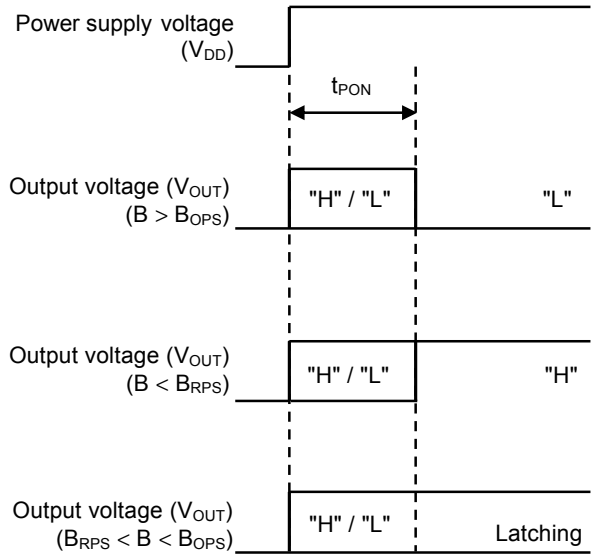
Figure 14

4. Timing chart

Figure 15 shows the operation timing at power-on.
The initial output voltage at rising of power supply voltage (V_{DD}) is either "H" or "L".

In case of $B > B_{OPS}$ (operation point) or $B < B_{RPS}$ (release point) at the time when the start up time (t_{PON}) is passed after rising of V_{DD}, this IC outputs V_{OUT} according to the applied magnetic flux density.
In case of $B_{RPS} < B < B_{OPS}$ at the time when t_{PON} is passed after rising of V_{DD}, this IC maintains the initial output voltage.

Product with S pole detection and active "L"



Product with S pole detection and active "H"

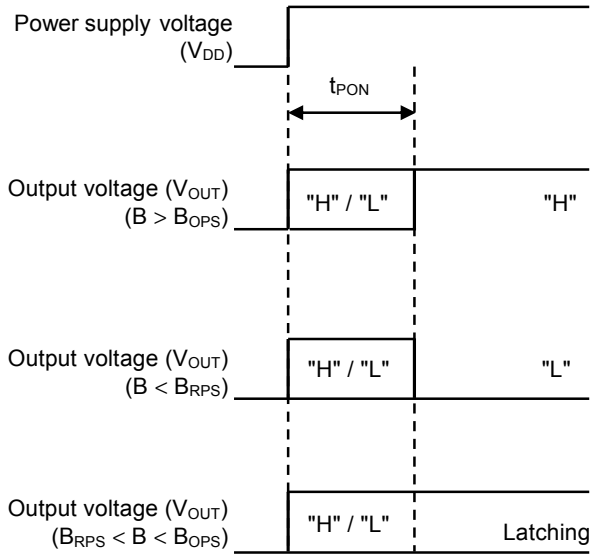


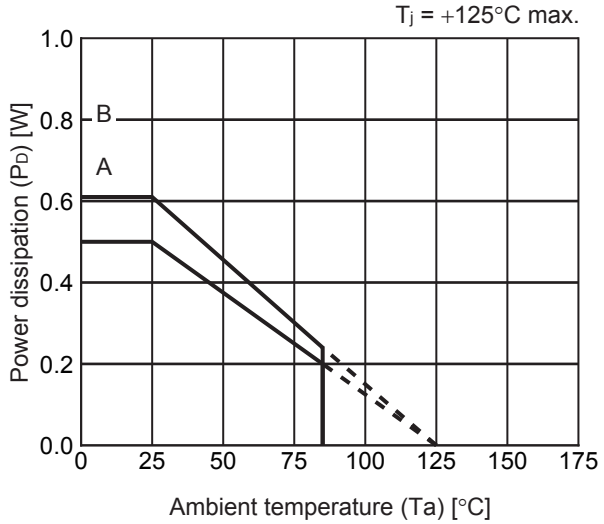
Figure 15

■ Precautions

- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by feed-through current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes. When the IC is used under the environment where the power supply voltage rapidly changes, it is recommended to judge the output voltage of the IC by reading it multiple times.
- Note that the output voltage may rarely change if the magnetic flux density between the operation point and the release point is applied to this IC continuously for a long time.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Although this IC has a built-in output current limit circuit, it may suffer physical damage such as product deterioration under the environment where the absolute maximum ratings are exceeded.
- The application conditions for the power supply voltage, the pull-up voltage, and the pull-up resistor should not exceed the power dissipation.
- Large stress on this IC may affect on the magnetic characteristics. Avoid large stress which is caused by the handling during or after mounting the IC on a board.
- SII Semiconductor Corporation claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Power Dissipation

SOT-23-3

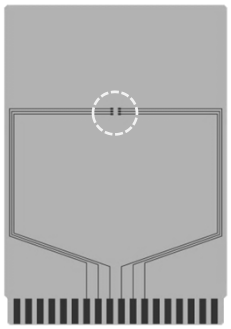


Board	Power Dissipation (P_D)
A	0.50 W
B	0.61 W
C	–
D	–
E	–

SOT-23-3/5/6 Test Board

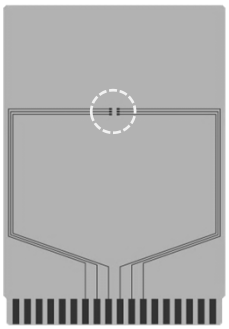
IC Mount Area

(1) Board A



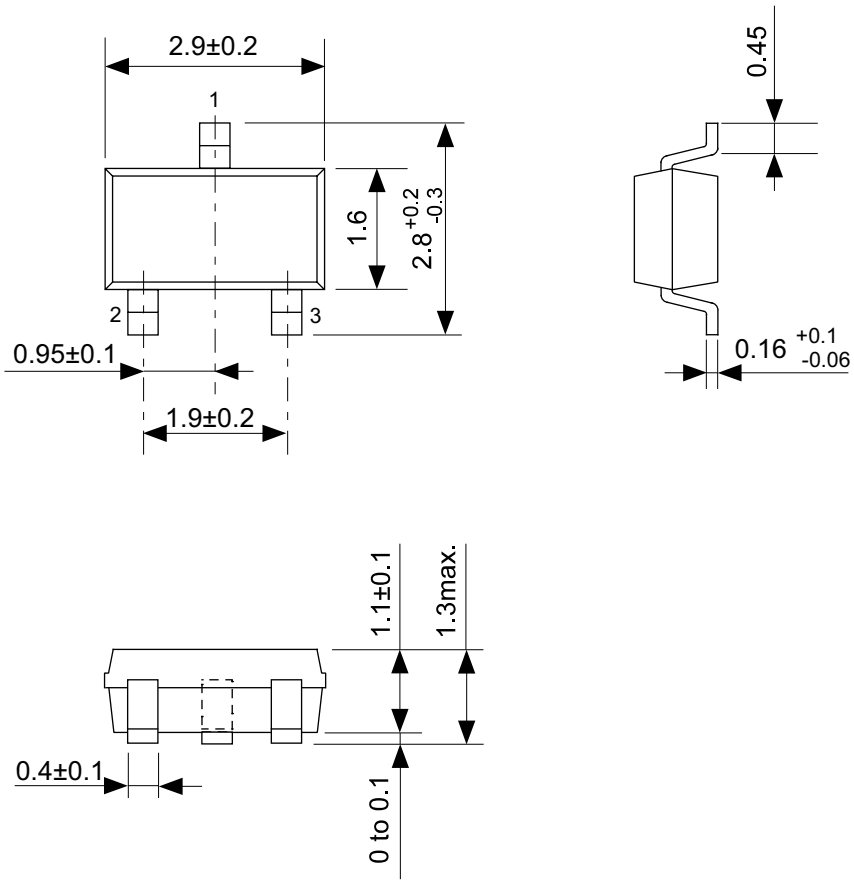
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



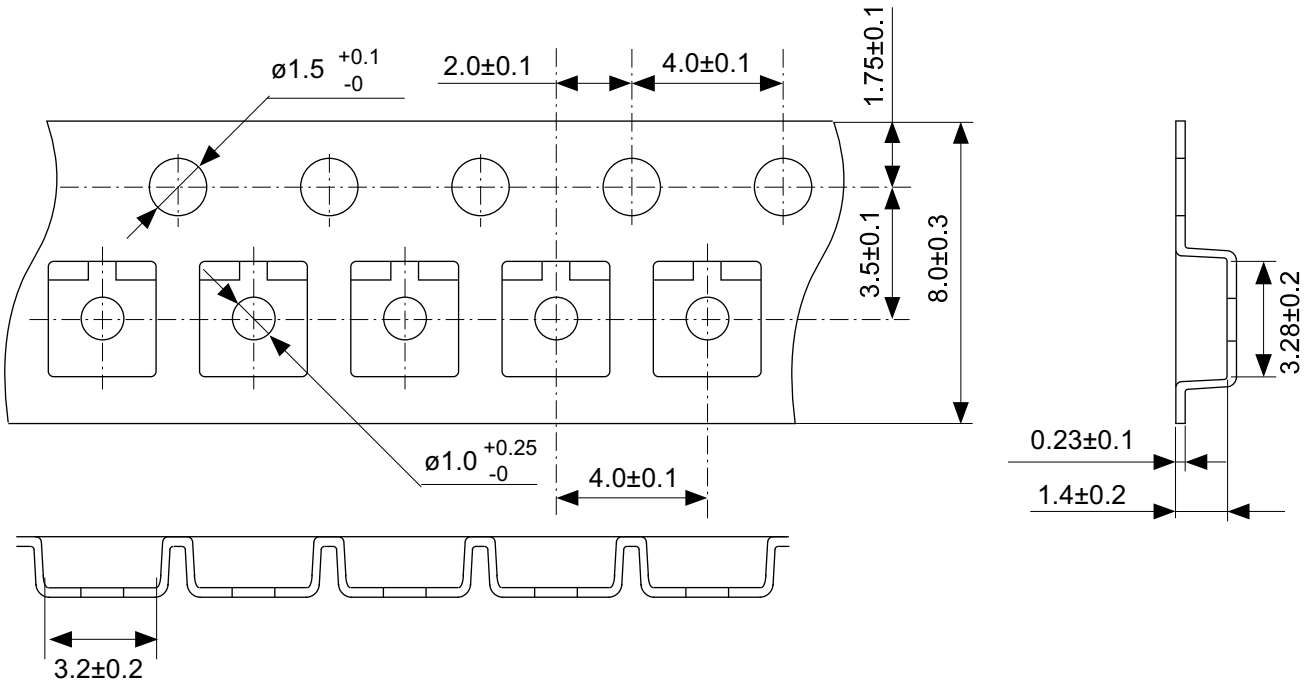
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

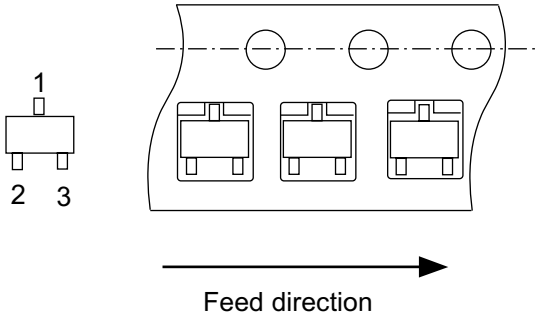
No. SOT23x-A-Board-SD-1.0



No. MP003-C-P-SD-1.1

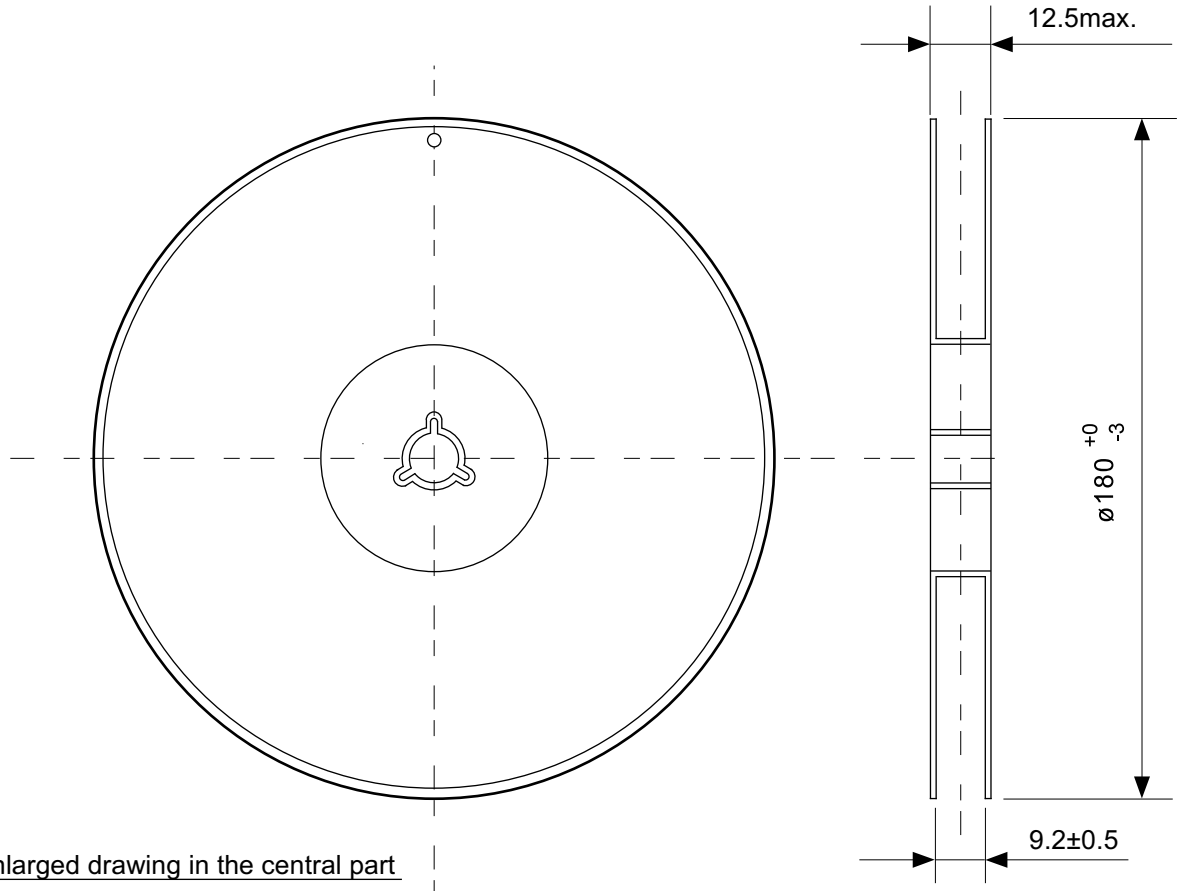
TITLE	SOT233-C-PKG Dimensions
No.	MP003-C-P-SD-1.1
ANGLE	
UNIT	mm
SII Semiconductor Corporation	



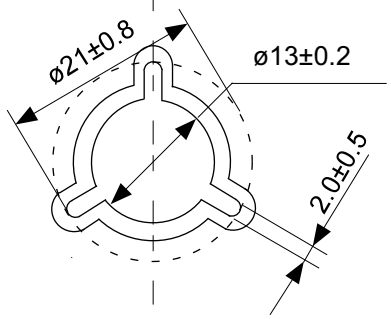


No. MP003-C-C-SD-2.0

TITLE	SOT233-C-Carrier Tape
No.	MP003-C-C-SD-2.0
ANGLE	
UNIT	mm
SII Semiconductor Corporation	



Enlarged drawing in the central part



No. MP003-Z-R-SD-1.0

TITLE	SOT233-C-Reel		
No.	MP003-Z-R-SD-1.0		
ANGLE		QTY.	3,000
UNIT	mm		
SII Semiconductor Corporation			

Disclaimers (Handling Precautions)

1. All the information described herein (product data, specifications, figures, tables, programs, algorithms and application circuit examples, etc.) is current as of publishing date of this document and is subject to change without notice.
2. The circuit examples and the usages described herein are for reference only, and do not guarantee the success of any specific mass-production design.
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